

EAST Search History**EAST Search History (Prior Art)**

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|--------------|-------------|---|---|-------------------------|----------------|---------------------|
| S21 | 9114 | gate and substrate and dielectric near5 electrode near5 capacit\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S22 | 2580 | S21 and sens\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S23 | 4641 | 257/296.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S24 | 1134 | 257/303.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S25 | 659 | 257/304.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S26 | 2648 | 257/306.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S27 | 902 | 257/309.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S28 | 1788 | 257/292.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S29 | 1539 | 257/e27.016.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |

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| S30 | 216 | 257/e27.017.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S31 | 61 | 257/e27.019.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S32 | 0 | 257/e27.020.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S33 | 183 | 257/e27.021.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S34 | 2 | ("6114862").PN. | USPAT; EPO; JPO; DERWENT | OR | OFF | 2009/09/24 12:08 |
| S35 | 2 | S34 and dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S36 | 0 | S34 and dielectric and capacitor and conductive near2 region and capacitive near2 electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S37 | 0 | S34 and dielectric and capacitor and conductive near2 region and capacitive near2 electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S38 | 0 | S34 and dielectric and capacitor and conductive near2 region and electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S39 | 0 | S34 and dielectric and capacitor and conduct\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |
| S40 | 2 | S34 and dielectric and capacitor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:08 |

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| S41 | 2403 | capacitive near5 sensor near5 circuit | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:43 |
| S42 | 2 | ("6423995").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2009/09/24 12:46 |
| S43 | 0 | ("l2and@ad<=19990726").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2009/09/24 12:53 |
| S44 | 2 | S42 and @ad<="19990726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:53 |
| S45 | 0 | (IC chip die (semiconductor adj device)) same (capacit\$3 near10 electrode) with (dielectric insulat\$3) same (sens\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:56 |
| S46 | 108 | (IC chip die (semiconductor adj device)) same (capacit\$3 near10 electrode) with (dielectric insulat\$3) same (sens\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:56 |
| S47 | 0 | S46 and @ad<="1990726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:56 |
| S48 | 42 | S46 and @ad<="19990726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:56 |
| S49 | 1315 | ((capacit\$3 near2 electrode) and (sens \$4 near5 surface) and (dielectric insulat\$3) and (IC chip die (semiconductor adj device))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 12:59 |
| S50 | 282 | ((capacit\$3 near2 electrode) and (sens \$4 near5 surface) and (dielectric insulat\$3) and (IC chip die (semiconductor adj device)) and ((conduct\$3 metal) near5 (plug region filler))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 13:01 |
| S51 | 292 | ((capacit\$3 near2 electrode) and (sens \$4 near5 surface) and (dielectric insulat\$3) and (IC chip die (semiconductor adj device)) and ((conduct\$3 metal) near5 (plug region filler))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 13:02 |

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| S52 | 312 | (S49 S50 S51) and @ad<="19990726" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 13:03 |
| S53 | 644 | 348/302.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/09/24 13:11 |

9/ 28/ 09 4:26:48 PM**C:\ Documents and Settings\ vtrinh\ My Documents\ EAST\ workspaces\ 10059982.wsp**